

RBV800D - RBV810D

PRV : 50 - 1000 Volts

Io : 8.0 Amperes

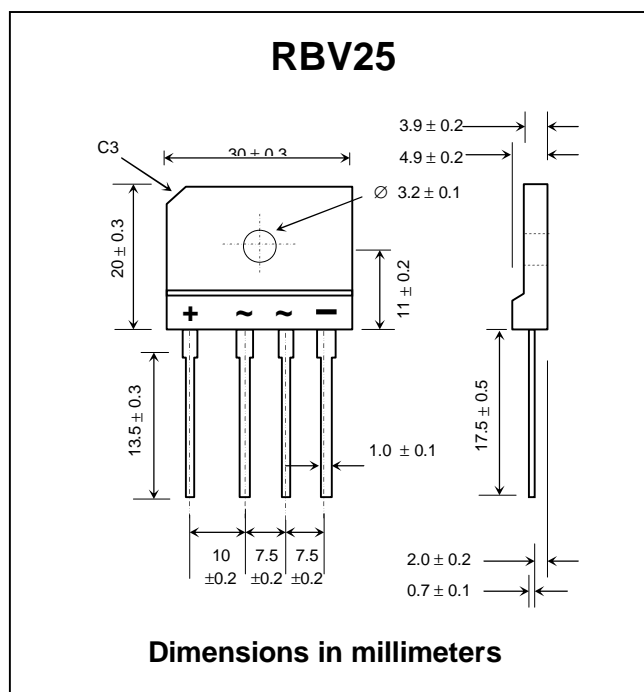
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * High case dielectric strength of 2000 V_{DC}
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 7.97 grams (Approximately)

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	RBV 800D	RBV 801D	RBV 802D	RBV 804D	RBV 806D	RBV 808D	RBV 810D	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current T _c = 55°C	I _{F(AV)}				8.0				A
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I _{FSM}				300				A
Current Squared Time at t < 8.3 ms.	I ² t				166				A ² S
Maximum Forward Voltage per Diode at I _F = 8.0 A	V _F				1.0				V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I _R	T _a = 25 °C			10				μA
		T _a = 100 °C			200				μA
Typical Thermal Resistance (Note 1)	R _{θJC}				2.2				°C/W
Typical Thermal Resistance at Junction to Ambient	R _{θJA}				15				°C/W
Operating Junction Temperature Range	T _J				- 40 to + 150				°C
Storage Temperature Range	T _{STG}				- 40 to + 150				°C

Notes :

1. Thermal Resistance from junction to case with units mounted on a 3.2"x3.2"x0.12" THK (8.2cm.x8.2cm.x0.3cm.) Al. Plate. heatsink.

RATING AND CHARACTERISTIC CURVES (RBV800D - RBV810D)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

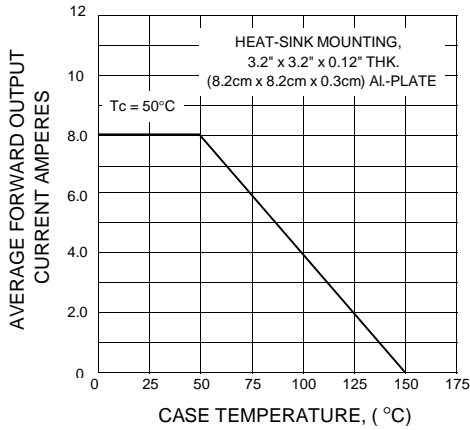


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

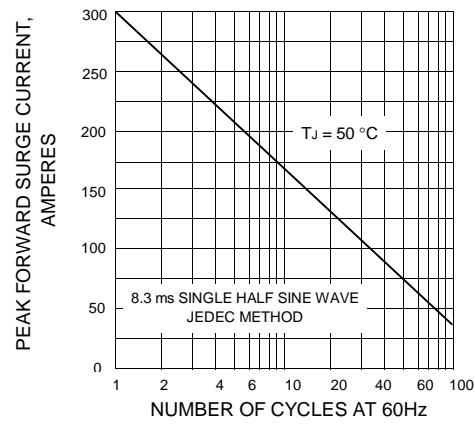


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

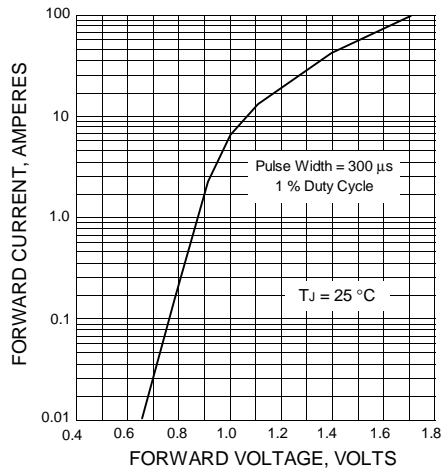


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

